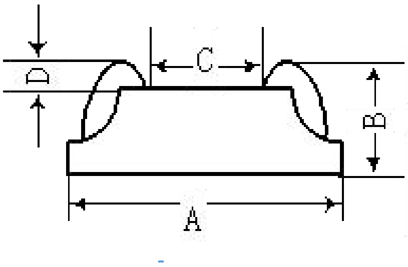
EPI chip (epitaxial chip)

VOLTAGE 100 to 800 Volts
CURRENT 1.0~10.0 Amperes



Dimension Part number	A	B	C	D
	Limits ±$^{1}_{2}$	Limits ±2	Limits ±3	Limits ±1
1A	50	12	27	2
2~4A	64	12	41	2
3~6A	72	12	49	2
5~8A	84	12	61	2
8~10A	95	12	72	2

Parameter	Symbol	SF50	SF64	SF72	SF84	SF95	Unit
Peak Inverse V	PIV	100 ~ 800					Volts
Forward Current	IF	1	3	5	8	10	Amps
Forward Volts	VF	PIV：200V VF spec. 0.9 PIV：400V VF spec. 1.25 PIV：600V VF spec. 1.7 PIV：800V VF spec. 2.2					Volts
Reverse recovery time	TRR	20~35					ns
Surge Current	IFSM	30	100	125			Amp/8.3ms
Leakage at 100℃	IRFM	400					uA
Junction Temp	TJ,MAX	150					Degrees ℃
Leakage 25℃	IRFM	10.0					uA
Storage Temp	TST	-65 ------- 150					Degrees ℃
Die Attach Temp	TD	340~375					Degrees ℃/2 min

The TRR waveform has smaller oscillations (less interference)

Our company provides PG photolithography process,
Guest system requirements for electrical properties;
Low temperature rise product;
High power products
White / gold diffusion products;